

A Thermagnonic Mechanism for Spin-Transfer Torque (STT)

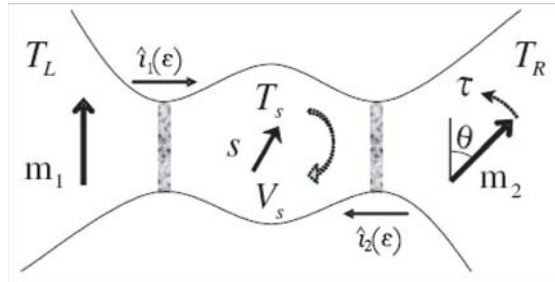
J. Slonczewski, Phys. Rev. B **82**, 054403 (2010)

Outline

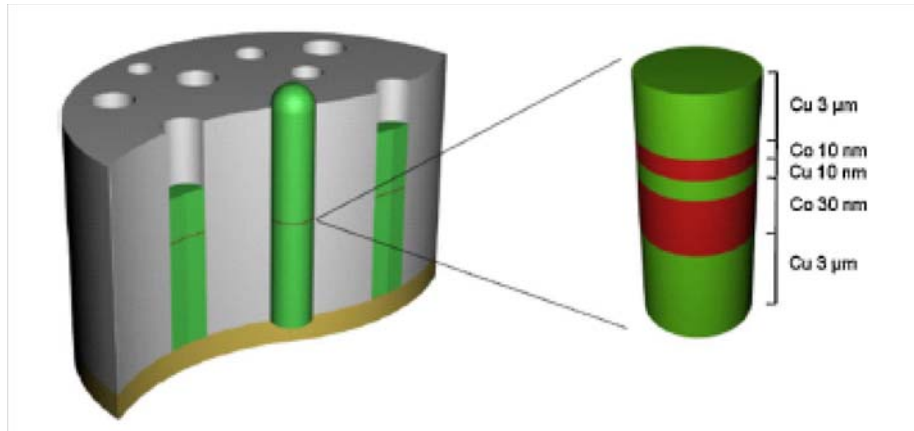
- Background of thermal STT mechanisms
- Physics of thermagnonic spin transfer
- An estimate of in-plane torque yield
- A crucial question of electron structure
- Summary

Background of spin transfer driven by heat flow

- **Theoretical prediction of spin-transfer torque driven by heat flow through an all-metallic multilayer:** M. Hatami, G. E. W. Bauer, Q. Zhang, and P. J. Kelly, Phys. Rev. Lett. **99**, 066603 (2007).

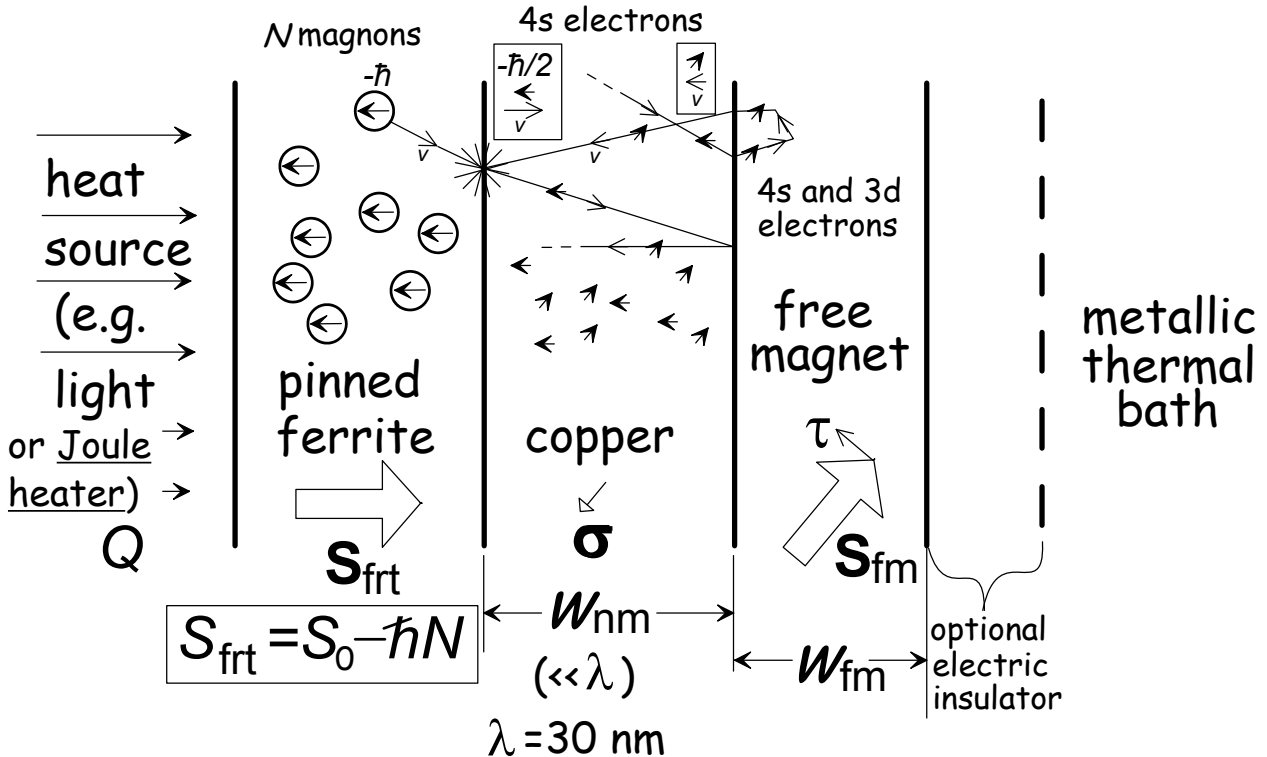


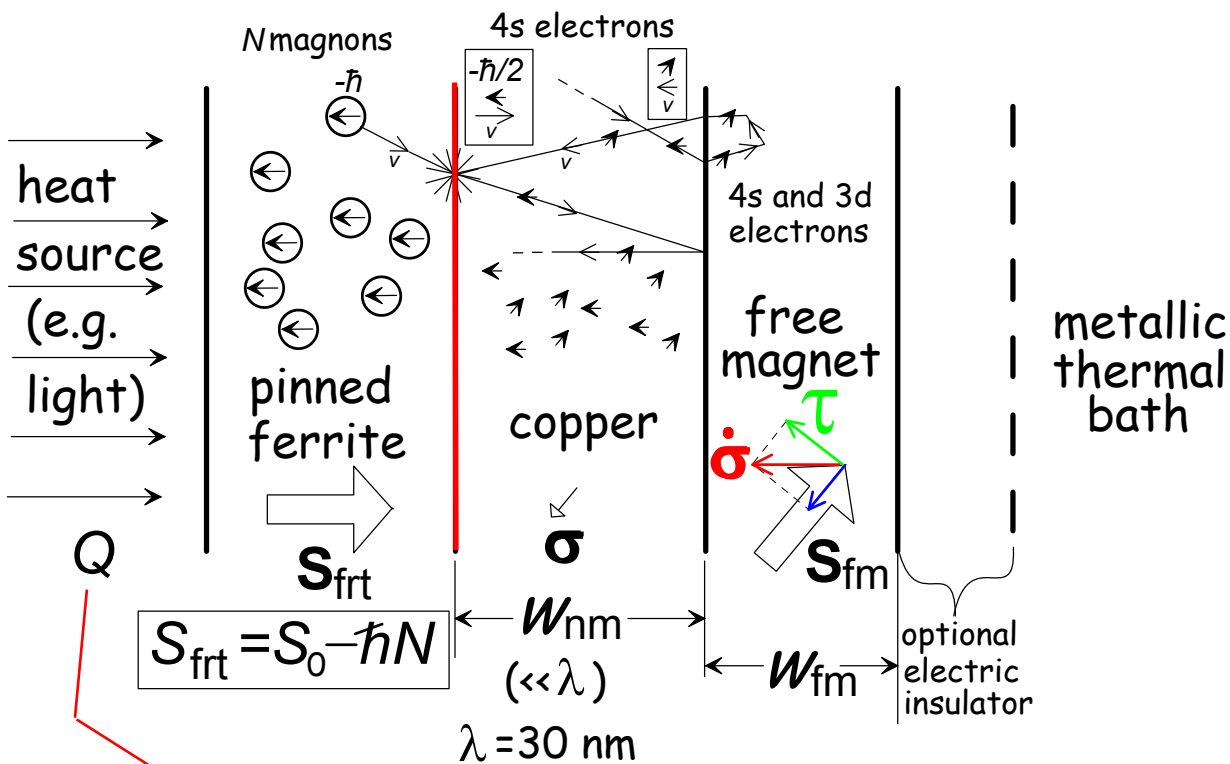
- **Observation of magnetic-field switching assisted by heat flow in an all-metallic multilayer:** H. Yu, S. Granville, D. P. Yu, and J. P. Ansermet, Phys. Rev. Lett. **104**, 146601 (2010).



Physics of thermagnonic spin transfer

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heat flow from Joule heater: $Q = IV$

σ = spin moment of $4s$ (free) electrons

$\dot{\sigma}$ = spin current at ferrite/copper interface

$$\tau = \dot{\sigma} \sin \theta$$

Quantum torque yield

Define a numerical quantum yield ε of current-driven spin-transfer torque by the output-to-input ratio

$$\varepsilon = \left| \frac{\text{transferred spin momentum}}{\hbar} \div \frac{\text{spent electric charge}}{e} \right|$$

for $\sin\theta = \pi/2$. For a magnetic tunnel junction (MTJ), $\varepsilon_{\text{mtj}} \leq 1/2$.

Quantum yield permitted by ferrite/noble-metal interface

Assume the presence of an octahedral-site magnetic monolayer with 3d spins S_j at the ferrite/noble-metal interface.

Spin operator is $\hbar S_j$ ($j = 1, 2, \dots, N_d$),

Effective molecular-field exchange energy is $-\mathbf{F}(T) \cdot \mathbf{S}_j$.

The system includes the magnetic monolayer and conduction electrons of the noble-metal film. The hamiltonian is

$$H = -\mathbf{F} \cdot \sum_{j=1}^N \mathbf{S}_j - (J_{sd}/n) \sum_{i,j} \mathbf{s}_i \cdot \mathbf{S}_j + \sum_{i=1}^n (\mathbf{p}_i^2/2m_e).$$

The transition $\Delta m_j = \pm 1$ in the magnetic energy $-Fm_j$ ($m_j = -S, -S + 1, \dots, S$) of the j -th interfacial atomic moment determines the inherent quantum yield. This inherent yield amounts to

$$\varepsilon_{\text{inh}} = |eV/F| \approx 10^2 V$$

Thus the interface permits a large inherent yield.

Useful quantum yield

But alas, in practice the inherent yield $\varepsilon_{\text{inh}} = e|V|/F$ is not available. The interfacial heat flow via phonons (Kapitza) exceeds that via magnons. The *useful* quantum yield is reduced in proportion to the respective interfacial thermal conductances:

$$\varepsilon_{\text{us}} = |eV|/F [1 + (G_{\text{Kap}}/G_{\text{fs}})]^{-1}, \quad G_{\text{fs}} = (G_{\text{fd}}^{-1} + G_{\text{ds}}^{-1})^{-1}$$

Define the thermal s-electron spin moment: $\sigma = \left\langle \sum_i^N s_i \right\rangle$

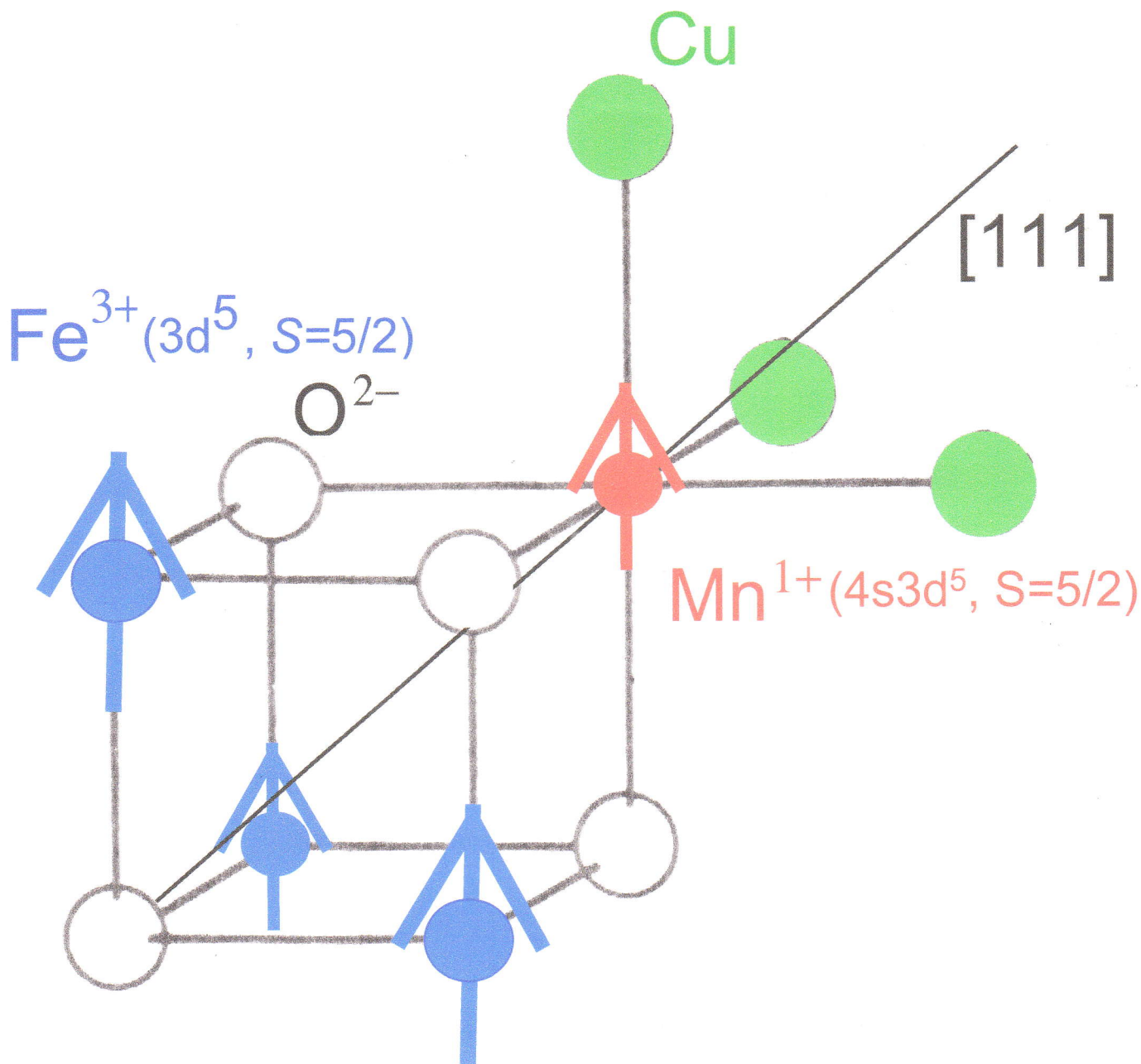
Bloch-type dynamic equation (Hasegawa, 1959):

$$\dot{\sigma} + \lambda \left\langle \sum_j \mathbf{S}_j \right\rangle \times \sigma = v_{\text{ds}} \left(\left\langle \sum_j \mathbf{S}_j \right\rangle - \left\langle \sum_j \mathbf{S}_j \right\rangle_{\text{equil}} \right) - v_s \sigma.$$

The d-to-s spin-relaxation rate (Korringa) is

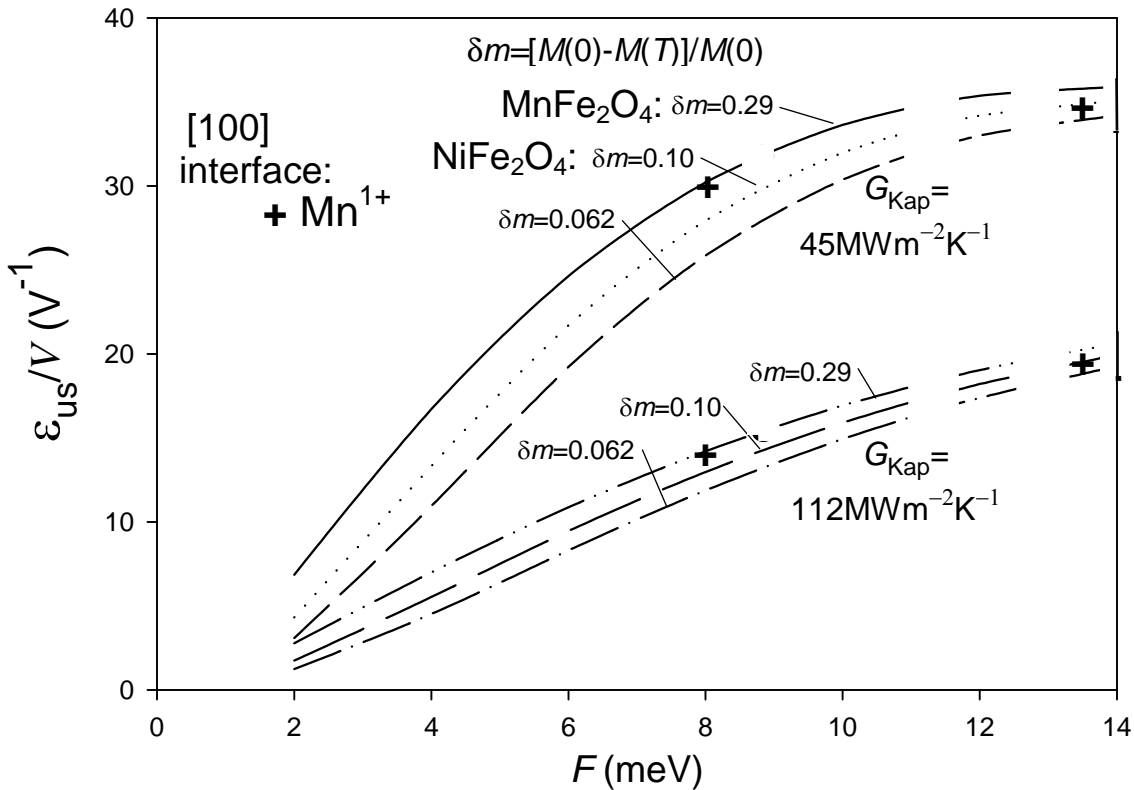
$$v_{\text{ds}} = (\pi/\hbar)(J_{\text{sd}}\rho)^2 k_{\text{B}} T,$$

interface: $\text{MnFe}_2\text{O}_4|\text{Mn}|\text{Me}$



Electron Structure of Mn

known	known	plausibly inferred
in ionic ferrite	impurity in metal	in interface
$Mn^{2+}, 3d^5$	$Mn^0, (4sp)^2 3d^5$	$Mn^{1+}, (4sp)^1 3d^5$
$S = 5/2$	$5/2$	$5/2$
electrons = 5	7	6



Summary and discussion

- For thermagnonic spin transfer one must make two replacements:
pinned magnet: metallic \Rightarrow ferrimagnetic
driving flow: electricity \Rightarrow heat
- In-plane torque for thermagnonic spin transfer:

$$\tau_{\text{tmg}} = \pm \varepsilon_{\text{us}} \hbar |I/e| (\mathbf{m}_{\text{ref}} \times \mathbf{m}_{\text{fm}}) \times \mathbf{m}_{\text{fm}}. \quad (\varepsilon_{\text{us}} \propto V)$$

- Thermagnonic spin transfer may provide a significant increase of available torque in nano devices: $\varepsilon_{\text{us}} \gg \varepsilon_{\text{mtj}}$
- One disadvantage for MRAM and storage devices is that the torque does not reverse with the sign of the driving current.
- A time delay (perhaps 1 ns per nm of ferrite thickness) needs investigation.